IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

- 1. (Cancelled)
- 2. (Previously Presented) The device manufacturing method of Claim 13, wherein said first layer of radiation sensitive material has a dose size of approximately 1.5 times to 2.5 times the magnitude of the dose size of said second layer of radiation sensitive material.
- 3. (Previously Presented) The device manufacturing method of Claim 13, wherein said first layer is thinner than said second layer.
- 4. (Previously Presented) The device manufacturing method of Claim 13, wherein said first layer is between 100 and 500nm thick and said second layer is between 500 and 1500 nm thick.
- 5. (Previously Presented) The device manufacturing method of Claim 13, wherein said first and second materials are substantially immiscible.
 - 6. (Cancelled)
- 7. (Currently Amended) [[A]] <u>The</u> device manufacturing method <u>of claim 13</u>, eomprising:

providing a substrate;

providing a first layer of electromagnetic radiation sensitive material on said substrate; providing a second layer of electromagnetic radiation sensitive material on said first layer of radiation sensitive material, the first and second layers of electromagnetic radiation sensitive material having a same tonality, said second layer of radiation sensitive material being of a different material than said first layer of radiation sensitive material, said first layer of radiation sensitive material, said first layer of radiation sensitive material having a dose size of at least approximately 1.5 times the magnitude of a dose size of said second layer of radiation sensitive material;

providing a beam of electromagnetic radiation using an illumination system;

imparting said beam of radiation with a desired pattern in its cross-section by employing a patterning device; and

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projecting said patterned beam of radiation onto a target portion of said substrate to expose both said first and second layers of radiation sensitive material,

wherein said first and second materials are based on bulky-acetal polymers.

- 8. (Currently Amended) The device manufacturing method of Claim [[7]] 13, wherein said first and second materials have different solvents.
 - 9. (Cancelled)
- 10. (Currently Amended) The device manufacturing method of Claim [[7]] 13, wherein said first and second layer materials are positively radiation sensitive.
 - 11. (Cancelled)
- 12. (Currently Amended) The device manufacturing method of Claim [[11]] 13, wherein said removed portion of said first layer is smaller than said removed portion of said second layer.
 - 13. (Previously Presented) A device manufacturing method comprising: providing a substrate;

providing a first layer of electromagnetic radiation sensitive material on said substrate;

providing a second layer of electromagnetic radiation sensitive material on said first layer of radiation sensitive material, the first and second layers of electromagnetic radiation sensitive material having a same tonality, said second layer of radiation sensitive material being of a different material than said first layer of radiation sensitive material, said first layer of radiation sensitive material having a dose size of at least approximately 1.5 times the magnitude of a dose size of said second layer of radiation sensitive material;

providing a beam of electromagnetic radiation using an illumination system;

imparting said beam of radiation with a desired pattern in its cross-section by employing a patterning device;

projecting said patterned beam of radiation onto a target portion of said substrate to expose both said first and second layers of radiation sensitive material; and

developing said first and second layers of radiation sensitive material to remove portions which have been exposed,

wherein said second layer overhangs said first layer after developing.

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- 14. (Cancelled)
- 15. (Cancelled)
- 16. (Previously Presented) A device manufacturing method comprising: providing a substrate;

providing a first layer of electromagnetic radiation sensitive material on said substrate;

providing a second layer of electromagnetic radiation sensitive material on said first layer of radiation sensitive material, the first and second layers of electromagnetic radiation sensitive material having a same tonality, said second layer of radiation sensitive material being of a different material than said first layer of radiation sensitive material, said first layer of radiation sensitive material having a dose size of at least approximately 1.5 times the magnitude of a dose size of said second layer of radiation sensitive material;

providing a beam of electromagnetic radiation using an illumination system;

imparting said beam of radiation with a desired pattern in its cross-section by employing a patterning device;

projecting said patterned beam of radiation onto a target portion of said substrate to expose both said first and second layers of radiation sensitive material;

developing said first and second layers of radiation sensitive material to remove portions which have been exposed;

depositing a first layer of metal onto said substrate;

lifting off said first and second layers of radiation sensitive material to leave a T-gate on said substrate; and

before said lifting off, depositing a second layer of metal onto said substrate.

- 17. (Original) The device manufacturing method of Claim 16, wherein said first layer of metal comprises Ti or Pt and said second layer comprises Pt or Au.
- 18. (Original) The device manufacturing method of Claim 16, further comprising depositing a third layer of metal onto said substrate.
- 19. (Original) The device manufacturing method of Claim 18, wherein said third layer of metal comprises Au.
 - 20. 21. (Cancelled)

- 22. (Cancelled).
- 23. (Previously Presented) The device manufacturing method of Claim 13, wherein said substrate comprises GaAs, Si, GaN, InP, or SiGa.
- 24. (Previously Presented) The device manufacturing method of Claim 13, wherein said method is a process for the manufacture of an integrated circuit having a T-gate.
 - 25. (Cancelled)
 - 26. (Cancelled)